

## Refine Search

### Search Results -

Terms	Documents
L2 and "first gate" and "second gate"	8

Database:

US Pre-Grant Publication Full-Text Database  
 US Patents Full-Text Database  
 US OCR Full-Text Database  
 EPO Abstracts Database  
 JPO Abstracts Database  
 Derwent World Patents Index  
 IBM Technical Disclosure Bulletins

Search:

L3





### Search History

 DATE: Thursday, September 16, 2004    [Printable Copy](#)    [Create Case](#)

<u>Set</u> <u>Name</u> side by side	<u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Name</u> result set
<i>DB=USPT; PLUR=YES; OP=OR</i>			
<u>L3</u>	L2 and "first gate" and "second gate"	8	<u>L3</u>
<u>L2</u>	("first gate dielectric" near6 (nitride near5 oxide)) and "second gate dielectric"	8	<u>L2</u>
<u>L1</u>	("first gate dielectric" near6 (ONO)) and "second gate dielectric"	0	<u>L1</u>

END OF SEARCH HISTORY